

PNP Silicon Epitaxial Planar Transistor

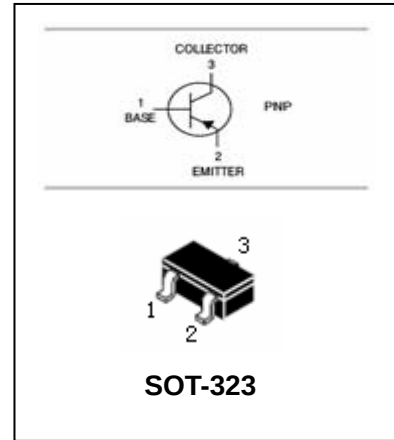
MMSTA55/MMSTA56

FEATURES

- Power dissipation.($P_C=200\text{mW}$).
- Epitaxial planar die construction.
- Also available in lead free version.



Lead-free



APPLICATIONS

- General purpose application and switching application.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMSTA55	K2H	SOT-323
MMSTA56	K2G	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage MMSTA55 MMSTA56	-60 -80	V
V_{CEO}	Collector-Emitter Voltage MMSTA55 MMSTA56	-60 -80	V
V_{EBO}	Emitter-Base Voltage MMSTA55 MMSTA56	-4	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

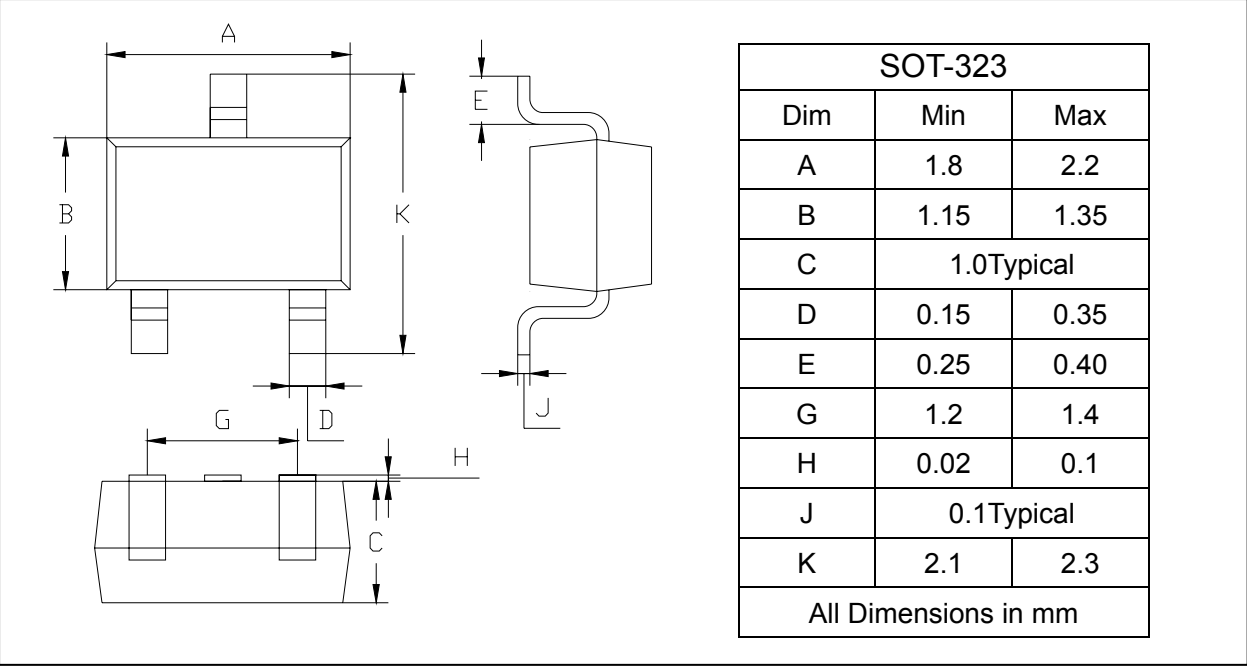
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$ MMSTA55 MMSTA56	-60 -80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$ MMSTA55 MMSTA56	-60 -80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$ MMSTA55 $V_{CB}=-80V, I_E=0$ MMSTA56			-0.1 -0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-50V, I_B=0$ MMSTA55 $V_{CE}=-60V, I_B=0$ MMSTA56			-0.1 -0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-10mA$ $V_{CE}=-1V, I_C=-100mA$	100 100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE}=-1V, I_C=-100mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-1V, I_C=-100mA,$ $f=100MHz$	50			MHz

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PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
MMSTA55/MMSTA56	SOT-323	3000/Tape&Reel